

5 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 28 October 2009

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: $I_{F(AV)} \le 5 A$
- Reverse voltage: $V_R \le 30 \text{ V}$
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz; T _{sp} ≤ 135 °C	-	-	5	A
V _R	reverse voltage		-	-	30	V
V _F	forward voltage	I _F = 5 A	-	400	450	mV
I _R	reverse current	V _R = 30 V	-	90	250	μΑ



5 A low V_F MEGA Schottky barrier rectifier

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	84
2	anode	1	1 1 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Order	ing inform	ation	
Type number	Package		
	Name	Description	Version
PMEG3050BEP	-	plastic surface-mounted package; 2 leads	SOD128

4. Marking

Table 4. Ma	rking codes	
Type number		Marking code
PMEG3050BE	þ	A8

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0, (,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C	-	30	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5;$ f = 20 kHz			
		$T_{amb} \le 20 \ ^{\circ}C$	<u>[1]</u> _	5	А
		$T_{sp} \le 135 \ ^{\circ}C$	-	5	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] _	70	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4] _	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

5 A low V_F MEGA Schottky barrier rectifier

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

[2] $T_j = 25 \ ^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	200	K/W
			<u>[4]</u> _	-	120	K/W
			[5] _	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

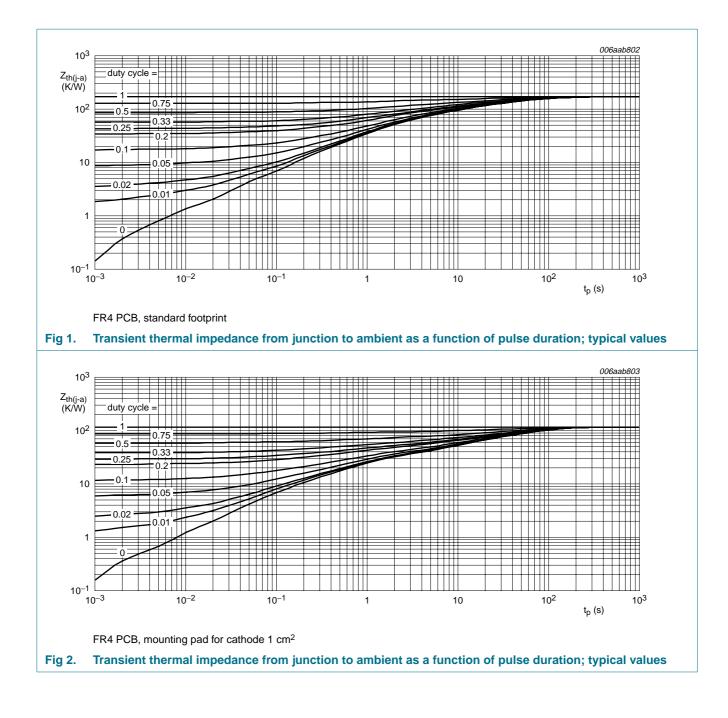
[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[5] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.

[6] Soldering point of cathode tab.

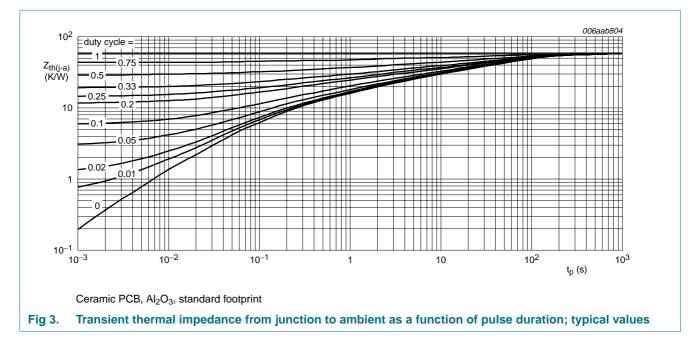
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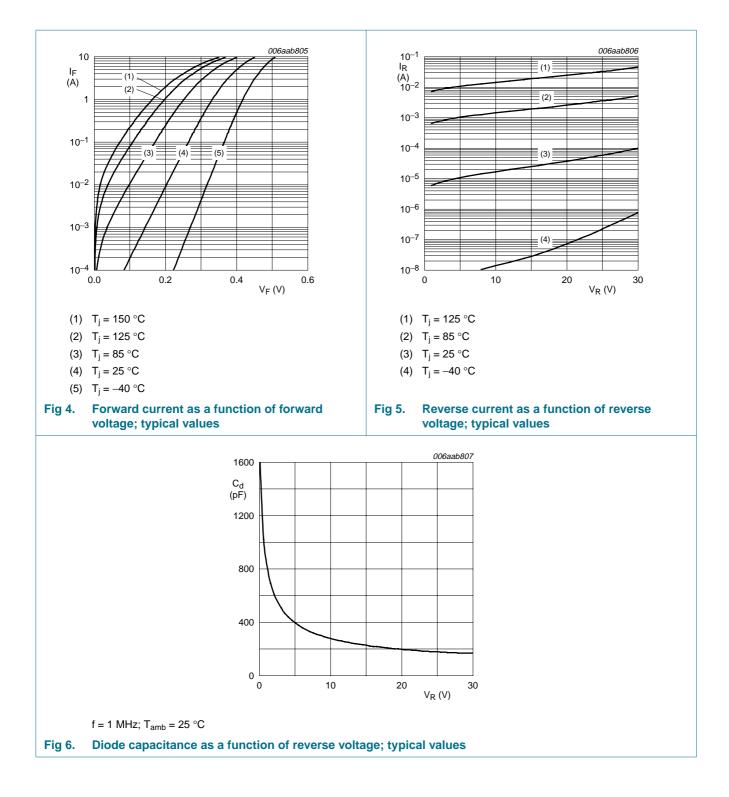
5 A low V_F MEGA Schottky barrier rectifier



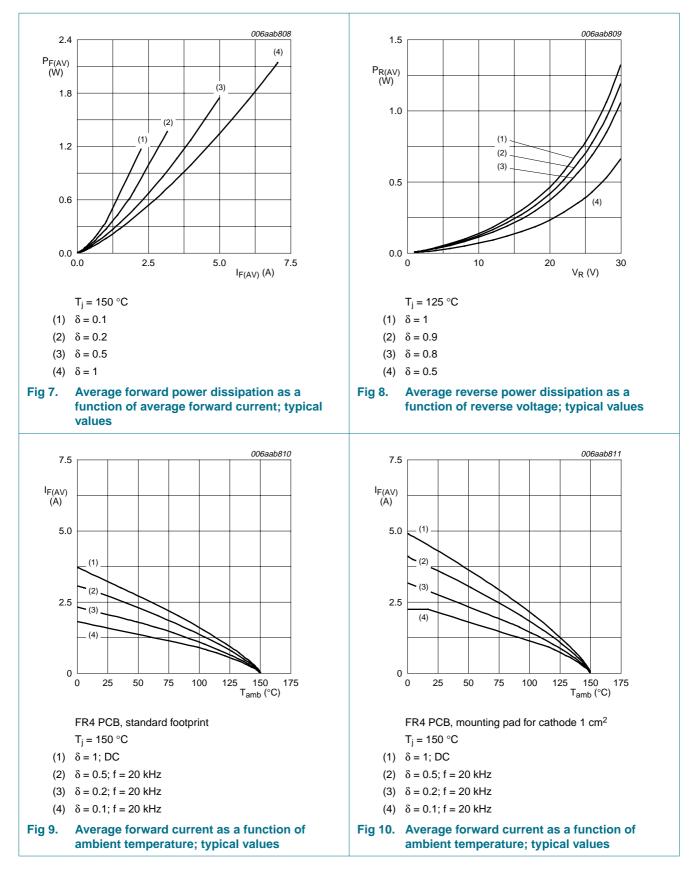
7. Characteristics

Table 7.Characteristics

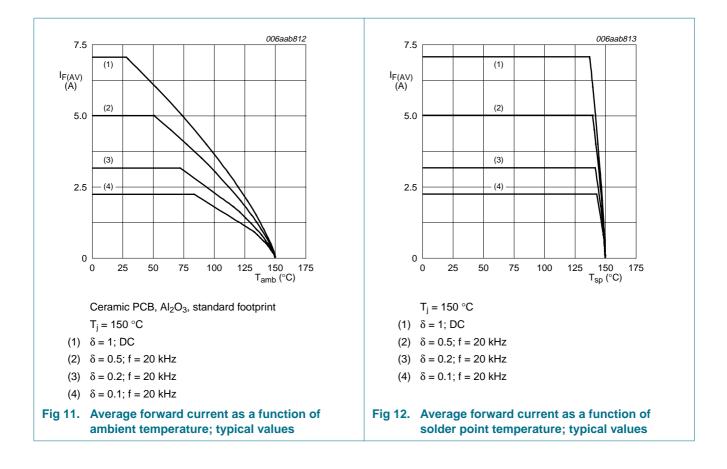
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 0.1 A	-	270	300	mV
		I _F = 0.5 A	-	315	360	mV
	I _F = 1 A	-	335	380	mV	
	I _F = 2 A	-	360	420	mV	
	I _F = 3 A	-	380	440	mV	
		I _F = 5 A	-	400	450	mV
I _R reverse current	reverse current	$V_R = 5 V$	-	10	-	μA
		V _R = 10 V	-	15	-	μA
		V _R = 30 V	-	90	250	μA
C _d	diode capacitance	f = 1 MHz				
		$V_R = 1 V$	-	800	-	pF
		V _R = 10 V	-	275	-	рF



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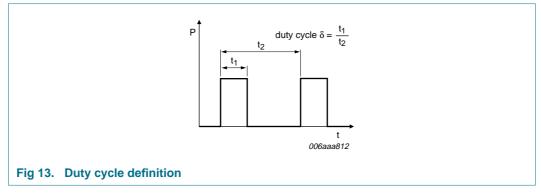


PMEG3050BEP



5 A low V_F MEGA Schottky barrier rectifier

8. Test information

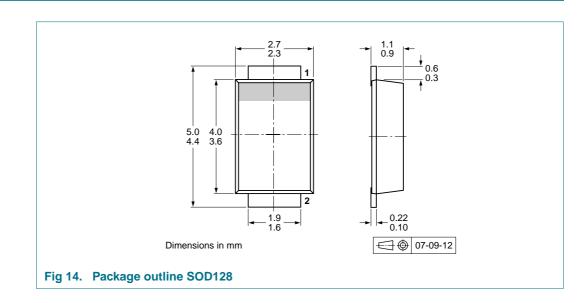


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



9. Package outline

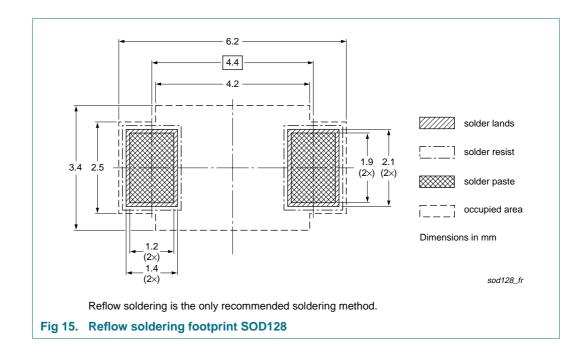
PMEG3050BEP 1

5 A low V_F MEGA Schottky barrier rectifier

10. Packing information

	i <mark>ng methods</mark> x are the last	t three digits of the 12NC ordering code.[1]	
Type number Package Description Packing quantity			
			3000
PMEG3050BEP	SOD128	4 mm pitch, 12 mm tape and reel	-115
[1] For further info	rmation and th	ne availability of packing methods, see Section 14.	

11. Soldering



5 A low V_F MEGA Schottky barrier rectifier

12. Revision history

Table 9. Revision hist	Revision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3050BEP_1	20091028	Product data sheet	-	-

5 A low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PMEG3050BEP_1
Product data sheet

5 A low V_F MEGA Schottky barrier rectifier

15. Contents

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Thermal characteristics 3
7	Characteristics 5
8	Test information 9
8.1	Quality information 9
9	Package outline 9
10	Packing information 10
11	Soldering 10
12	Revision history 11
13	Legal information 12
13.1	Data sheet status 12
13.2	Definitions 12
13.3	Disclaimers
13.4	Trademarks 12
14	Contact information 12
15	Contents 13

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